ESD/Surge Protection Diode Array

Bi-directional ESD Protection for High-Speed Data Line

SMDA05C Series

The SMDA05C surge protection series is designed to protect equipment attached to up to four high speed communication lines from ESD, EFT and surge.

Features

- SO-8 Package
- Peak Power 300 W 8 x 20 μs
- ESD Rating:

IEC 61000-4-2 (ESD) ±15 kV (Air) ±8 kV (Contact)

IEC 61000-4-4 (EFT) 40 A (5/50 ns)

IEC 61000-4-5 (Surge) 12 A (8/20 μs)

- UL Flammability Rating of 94 V-0
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- High Speed Communication Line Protection
- Data and I/O Lines
- Microprocessor Based Equipment
- LAN/WAN Equipment
- Servers
- Notebook and Desktop PC
- Serial and Parallel Ports
- Peripherals

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation 8 x 20 μs @ T _A = 25°C (Note 1)	P _{pk}	300	W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum 10 Seconds Duration	T _L	260	°C

1

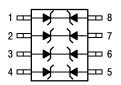


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SO-8 ESD AND SURGE PROTECTOR 300 WATTS PEAK POWER

PIN CONFIGURATION AND SCHEMATIC





SO-8 CASE 751-07

MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 3 of this data sheet.

^{1.} Non-repetitive current pulse 8 x 20 μs exponential decay waveform.

SMDA05C Series

SMDA05C ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Working Voltage	V _{RWM}	-	-	5.0	V
Reverse Breakdown Voltage @ I _t = 1.0 mA	V _{BR}	6.0	-	-	V
Reverse Leakage Current @ V _{RWM} = 5 Volts	I _R	N/A	-	20	μΑ
Maximum Clamping Voltage @ I _{PP} = 1.0 A, 8 x 20 μs	V _C	N/A	-	9.8	V
Maximum Clamping Voltage @ I _{PP} = 5.0 A, 8 x 20 μs	V _C	N/A	-	11	V
Maximum Peak Pulse Current, 8 x 20 μs	I _{PP}	-	-	17	Α
Junction Capacitance @ V _R = 0 V, f = 1 MHz	CJ	-	-	350	pF

SMDA12C ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Working Voltage	V _{RWM}	-	-	12	V
Reverse Breakdown Voltage @ I _t = 1.0 mA	V _{BR}	13.3	-	-	V
Reverse Leakage Current @ V _{RWM} = 12 Volts	I _R	N/A	-	1.0	μΑ
Maximum Clamping Voltage @ I _{PP} = 1.0 A, 8 x 20 μs	V _C	N/A	-	19	V
Maximum Clamping Voltage @ I _{PP} = 5.0 A, 8 x 20 μs	V _C	N/A	-	24	V
Maximum Peak Pulse Current, 8 x 20 μs	I _{PP}	-	-	12	Α
Junction Capacitance @ V _R = 0 V, f = 1 MHz	CJ	-	-	120	pF

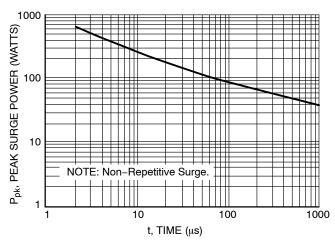
SMDA15C ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Working Voltage	V _{RWM}	-	-	15	V
Reverse Breakdown Voltage @ I _t = 1.0 mA	V _{BR}	16.7	-	-	V
Reverse Leakage Current @ V _{RWM} = 15 Volts	I _R	N/A	-	1.0	μА
Maximum Clamping Voltage @ I _{PP} = 1.0 A, 8 x 20 μs	V _C	N/A	-	24	V
Maximum Clamping Voltage @ I _{PP} = 5.0 A, 8 x 20 μs	V _C	N/A	-	30	V
Maximum Peak Pulse Current, 8 x 20 μs	I _{PP}	-	-	10	Α
Junction Capacitance @ V _R = 0 V, f = 1 MHz	CJ	-	-	75	pF

SMDA24C ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Working Voltage	V _{RWM}	-	-	24	V
Reverse Breakdown Voltage @ I _t = 1.0 mA	V _{BR}	26.7	-	-	V
Reverse Leakage Current @ V _{RWM} = 24 Volts	I _R	N/A	-	1.0	μΑ
Maximum Clamping Voltage @ I _{PP} = 1.0 A, 8 x 20 μs	V _C	N/A	-	43	V
Maximum Clamping Voltage @ I _{PP} = 5.0 A, 8 x 20 μs	V _C	N/A	-	55	V
Maximum Peak Pulse Current, 8 x 20 μs	I _{PP}	-	-	5.0	Α
Junction Capacitance @ V _R = 0 V, f = 1 MHz	CJ	-	_	50	pF

SMDA05C Series



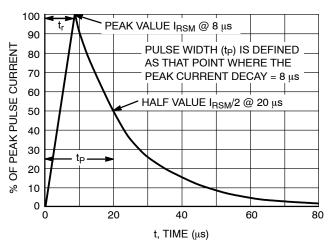


Figure 1. Pulse Width

Figure 2. $8\times 20~\mu s$ Pulse Waveform

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
SMDA05CDR2G	AAA	SO-8 (Pb-Free)	2500 / Tape & Reel
SMDA12CDR2G	AAC	SO-8 (Pb-Free)	2500 / Tape & Reel
SMDA15CDR2G	AAD	SO-8 (Pb-Free)	2500 / Tape & Reel
SMDA24CDR2G	AAE	SO-8 (Pb-Free)	2500 / Tape & Reel

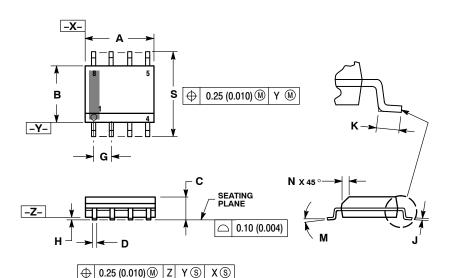
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





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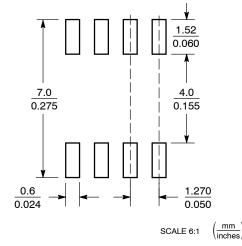
DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

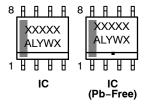
	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	7 BSC	0.050 BSC	
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
s	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

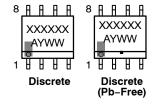
GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot

= Year = Work Week W

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SOIC-8 NB CASE 751-07 ISSUE AK

DATE 16 FEB 2011

			D/ (I E TO I ED E
STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1 STYLE 6:	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1 STYLE 7:	
PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	7. DHAIN 1 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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